KSD07N65

650V N-Channel MOSFET

General Description

The Power MOSFET is fabricated using the advanced VDMOS technology.

The resulting device has low conduction resistance, superior switching performance and high avalanche energy.

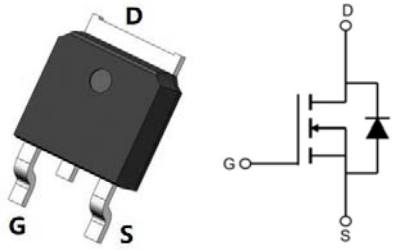
Product Summary

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
650	1.0at V_{GS} = 10 V	7

Features

- LOW ON-RESISTANCE
- FAST SWITCHING
- HIGH INPUT RESISTANCE

TO-252 Pin Configuration



Applications

- SWITCH MODE POWER SUPPLY
- ELECTRONIC BALLAST

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current – Continuous (T_C=25℃)	7.0	A
	Drain Current – Continuous (T_C=100℃)	3.0	A
I_{DM}	Drain Current – Pulsed[1]	25	A
P_D	Power Dissipation (T_C=25℃)	68	W
	Power Dissipation (T_C=100℃)	0.8	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	1.73	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	650	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=650V , V_{GS}=0V , T_J=25℃	---	---	5	uA
		V_{DS}=500V , V_{GS}=0V , T_J=125℃	---	---	20	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=3.0A	---	1.0	1.26	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2.0	3.0	4.0	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient					
gfs	Forward Transconductance	V_{DS}=30V , I_S=2A	---	17	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=400V , V_{GS}=10V , I_D=4A	---	16	---	nC
Q_{gs}	Gate-Source Charge[2,3]		---	5	---	
Q_{gd}	Gate-Drain Charge[2,3]		---	4.2	---	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DS}=250V, I_D=4A V_{GS}=10V,R_G=5Ω	---	12	---	ns
T_r	Rise Time[2,3]		---	43	---	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	52	---	
T_f	Fall Time[2,3]		---	40	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	1080	---	pF
C_{oss}	Output Capacitance		---	95	---	
C_{rss}	Reverse Transfer Capacitance		---	17	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	5	A
I_{SM}	Pulsed Source Current		---	---	15	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristics (Curves)

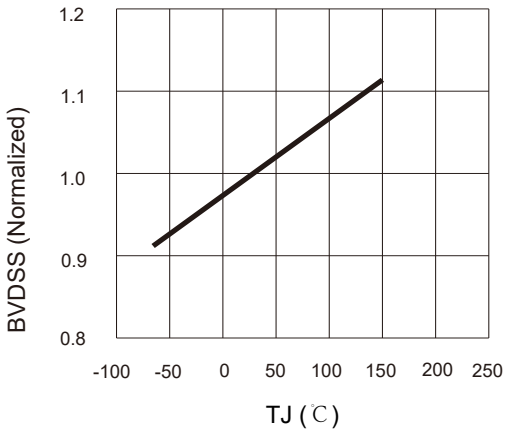


Figure 1: Break Down vs. Junction Temperature

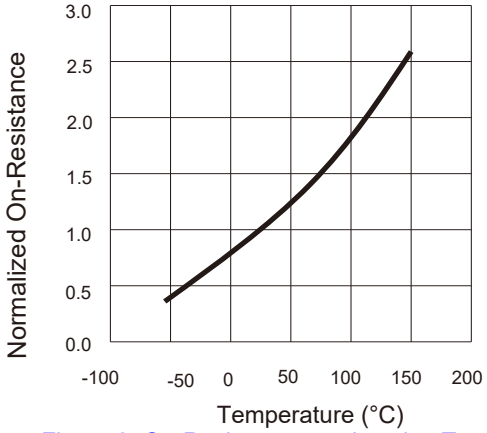
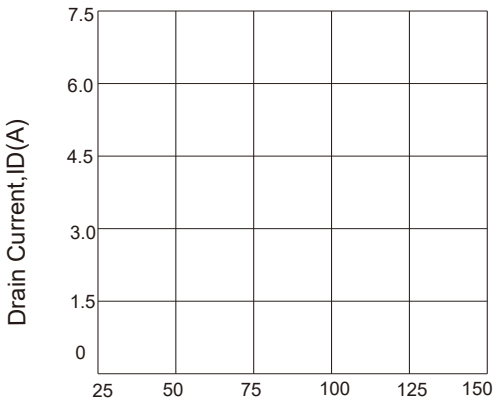


Figure 2: On-Resistance vs. Junction Temperature



On-State Characteristics

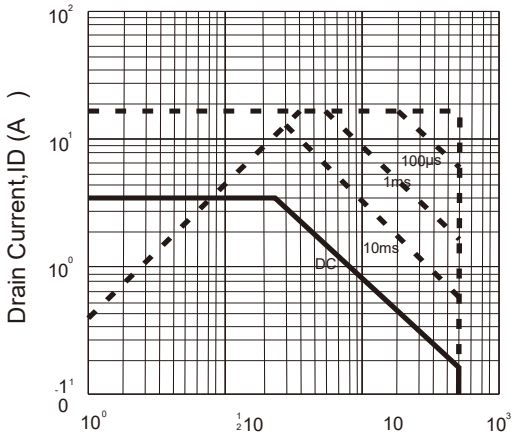
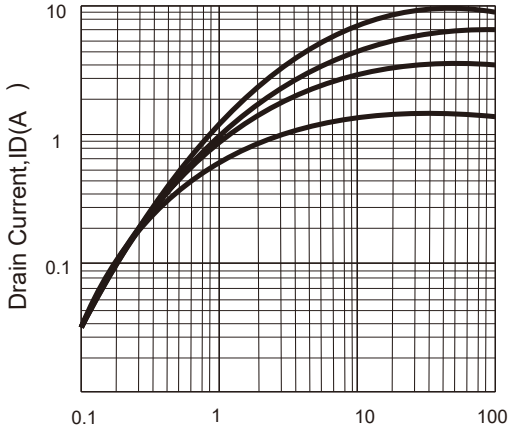
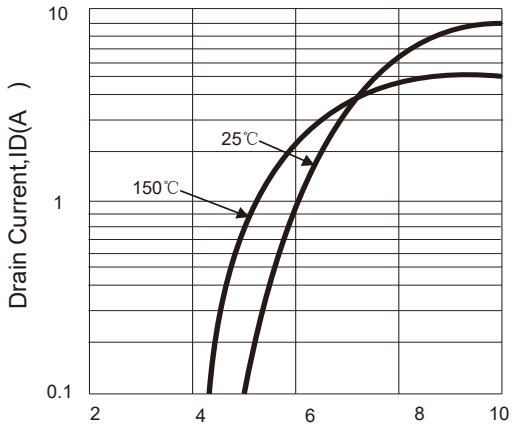


Figure 9: Maximum Forward Biased Safe Operating Area





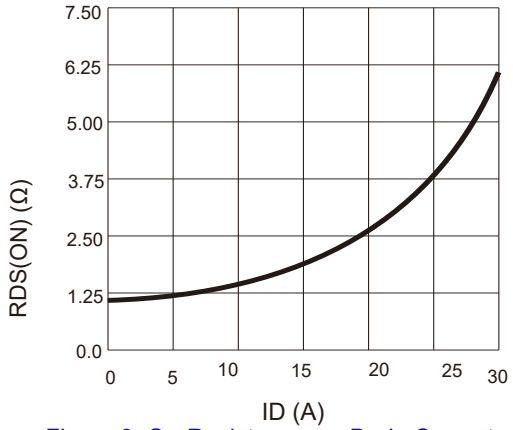


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

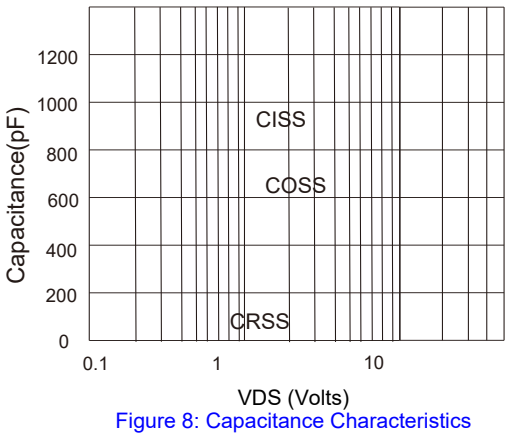


Figure 8: Capacitance Characteristics

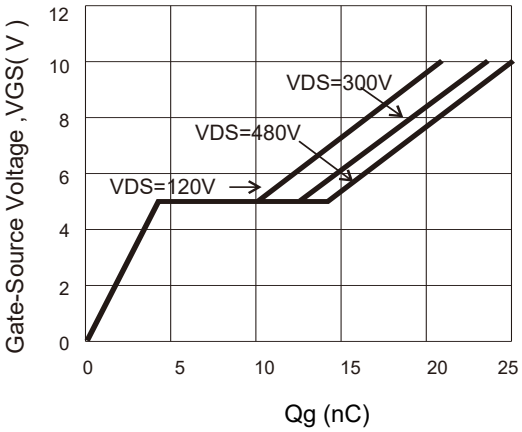


Figure 7: Gate-Charge Characteristics

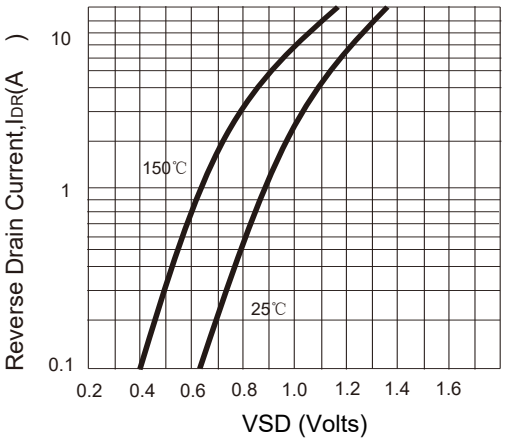


Figure 6: Body-Diode Characteristics

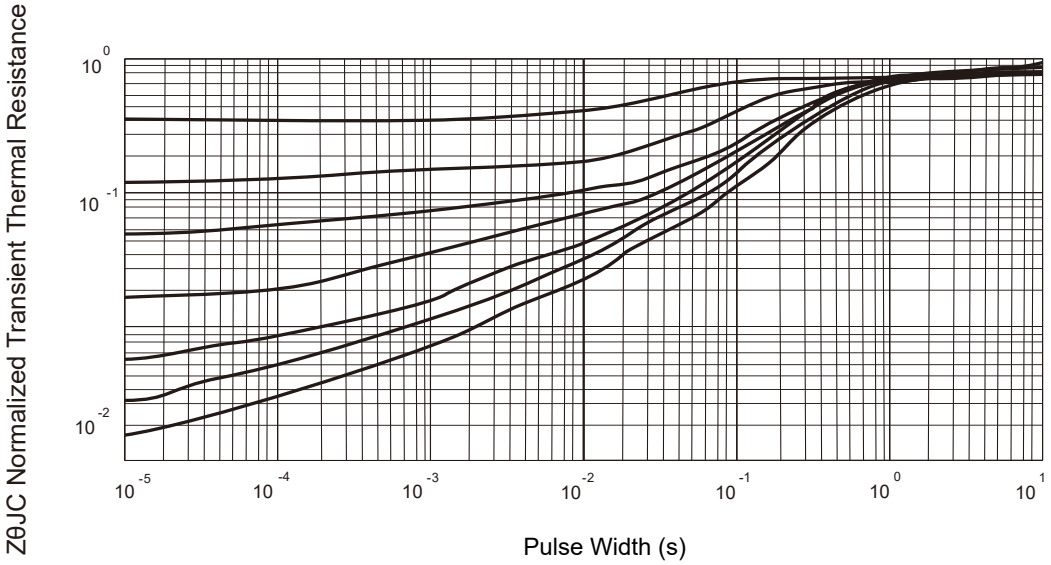


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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